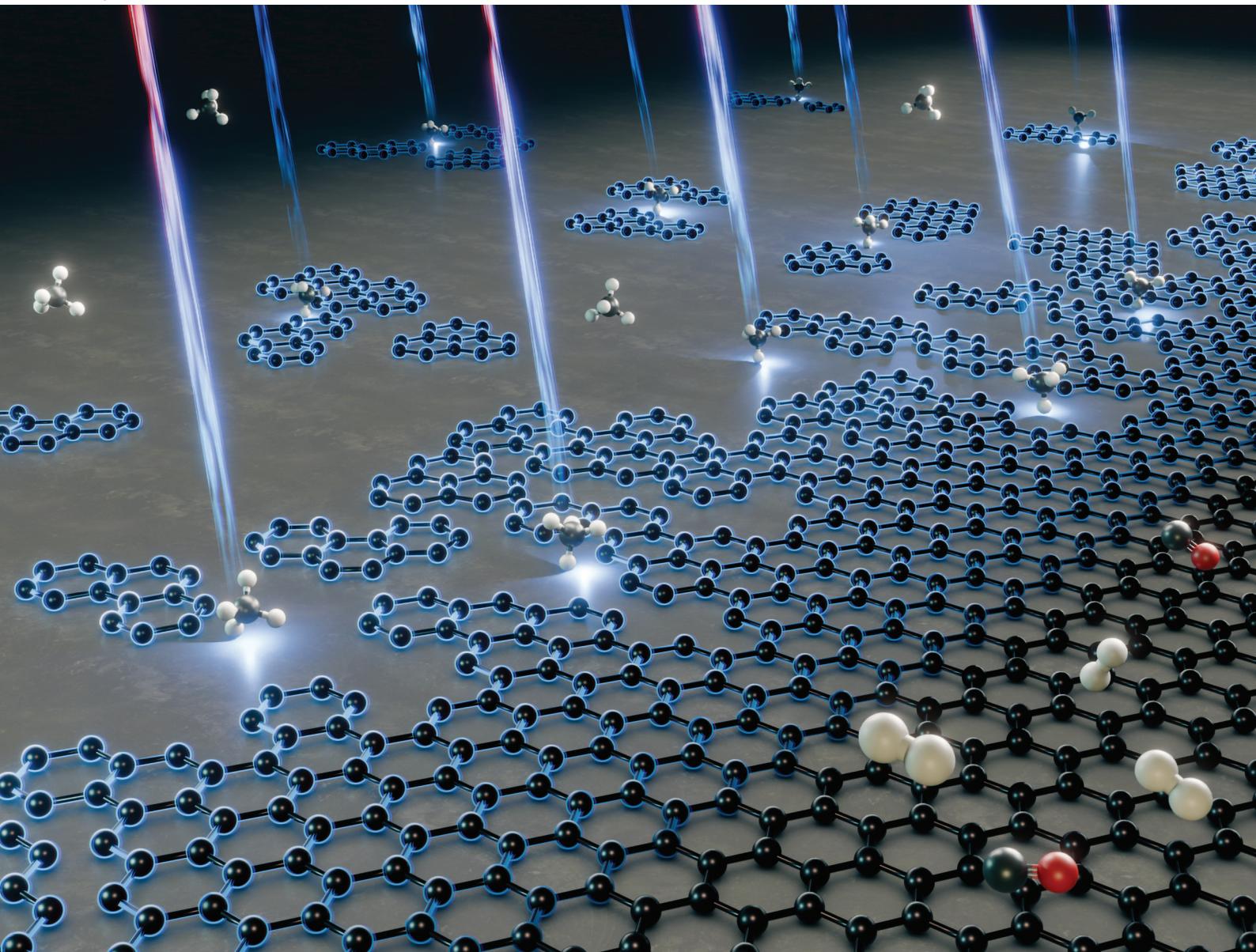


# Nanoscale

[rsc.li/nanoscale](http://rsc.li/nanoscale)



ISSN 2040-3372



Cite this: *Nanoscale*, 2025, **17**, 13646

## Mechanism of methane activation and graphene growth on oxide ceramics

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Three-dimensional (3D) graphene materials have attracted significant attention across various fields, including energy storage and catalysis, due to their exceptional properties such as developed nanoporosity, corrosion resistance, electrical conductivity, and mechanical flexibility. The first step in synthesizing nanoporous 3D graphene involves the generation of the graphene framework through the decomposition of methane at high temperatures on thermally stable oxide ceramics. Thus, a thorough understanding of the reaction mechanism involved in this initial step is crucial. This article reviews recent advancements in elucidating the mechanisms of methane activation and subsequent graphene growth on various types of oxide ceramics, including alumina ( $\text{Al}_2\text{O}_3$ ), magnesia ( $\text{MgO}$ ), calcium oxide ( $\text{CaO}$ ), and silica ( $\text{SiO}_2$ ).

Received 8th February 2025,  
Accepted 9th April 2025

DOI: 10.1039/d5nr00569h

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### 1. Introduction

Graphene is a remarkable carbon material characterized by a two-dimensional, monolayer structure in which carbon atoms are arranged in a hexagonal lattice *via*  $\text{sp}^2$  hybridization.<sup>1</sup> As one of the thinnest and lightest materials known, graphene exhibits exceptional properties, including high electrical conductivity, out-

standing electron mobility ( $2.5 \times 10^5 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ),<sup>2</sup> a large specific surface area ( $2627 \text{ m}^2 \text{ g}^{-1}$ ),<sup>3</sup> and remarkable thermal conductivity (over  $3000 \text{ W mK}^{-1}$ ).<sup>4</sup> Its unique characteristics make it highly versatile for a wide range of advanced applications, including biosensors,<sup>5</sup> solar cell electrodes,<sup>6</sup> and photocatalysts.<sup>7</sup> Recently, graphene has become capable of being mass-produced at a relatively low cost, enhancing its practical value. Spherical molecules composed of  $\text{sp}^2$  carbon, known as fullerenes,<sup>8</sup> and tubular structures, referred to as carbon nanotubes,<sup>9,10</sup> are zero-dimensional and one-dimensional graphene-related structures, respectively, each possessing unique characteristics distinct from two-dimensional graphene. Meanwhile, steady progress has recently been made in the synthesis of three-dimensional (3D) graphene structures, theoretically designed by incorporating heptagonal and octagonal rings into carbon hexagonal networks.<sup>11,12</sup> Among these developments, the “Graphene MesoSponge®

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(GMS)<sup>13</sup> recently developed by the authors, is a novel mesoporous material that strongly reflects the characteristic properties of graphene, such as high specific surface area, electrical conductivity, corrosion resistance, lightweight nature, and mechanical flexibility. It holds great potential for applications in various fields, including energy storage,<sup>14,15</sup> heat pumps,<sup>16</sup> and catalyst supports.<sup>17,18</sup>

This minireview primarily highlights recent advancements in the initial stage of GMS synthesis, specifically the chemical vapor deposition (CVD) process. The entire synthesis process of GMS will first be outlined, followed by an in-depth discussion of the CVD process, with an emphasis on the mechanism of graphene growth on the surface of oxide ceramics. Note that in this minireview, “CH<sub>4</sub> activation” refers to the initial catalytic weakening of C–H bonds, while “CH<sub>4</sub> decomposition” encompasses the entire process of CH<sub>4</sub> breakdown into carbon, either catalytic or non-catalytic thermal pathways.

## 2. Synthesis of three-dimensional graphene

Graphene can be synthesized by various methods, including mechanical cleavage,<sup>1</sup> chemical exfoliation,<sup>19,20</sup> epitaxial growth on SiC surfaces,<sup>21</sup> and CVD.<sup>22</sup> Among these, CVD is regarded as one of the most promising approaches for fabricating graphene-based 3D nanostructures. Since CVD promotes graphene growth along the substrate surface, removing the substrate after performing CVD on a 3D nanostructured substrate results in 3D graphene with a corresponding morphology.<sup>23–25</sup> The substrate used in CVD is referred to as the “template”. CVD needs to be conducted at high temperatures, typically around 600–900 °C to produce high-quality gra-

phene. Consequently, it is challenging to use metal nanostructures with a low melting point as templates, underscoring the need for templates with higher heat resistance. On the other hand, oxide ceramics exhibit excellent heat resistance and serve as templates even at CVD temperatures, allowing for relatively straightforward control over 3D nanostructures.

When Al<sub>2</sub>O<sub>3</sub> or zeolite is used as a catalyst for the organic compound conversion reactions at high temperatures, polycyclic aromatic hydrocarbons (coke) are produced as by-products and the catalytic activity is reduced. This phenomenon is widely known as “coking”. Coking causes poisoning of catalysts, and therefore, most researchers tried to avoid coking. On the other hand, Kyotani’s group pioneered the utilization of coking reactions for synthesizing templated carbons.<sup>26,27</sup> For example, intentional coke deposition, *i.e.*, CVD, inside the three-dimensional network pores of zeolites results in zeolite-templated carbon (ZTC),<sup>27</sup> consisting of a three-dimensional framework of single-layer graphene.<sup>25,28</sup> ZTC is, to the best of the authors’ knowledge, the most pioneering 3D graphene structure and continues to be actively studied worldwide.<sup>3</sup> However, ZTCs have low chemical stability due to the large amount of graphene edge sites. It will quickly degrade when applied to batteries and other devices.<sup>3</sup>

GMS overcomes this weakness of ZTC by removing edges to the maximum extent possible through a graphene fusion (zipping) reaction,<sup>29</sup> achieving chemical stability superior to that of carbon nanotubes.<sup>14,30</sup> Fig. 1 illustrates the formation of GMS. The typical synthesis of GMS begins with a CVD process using Al<sub>2</sub>O<sub>3</sub> and MgO nanoparticles as spherical templates and CH<sub>4</sub> as the carbon source.<sup>31</sup> After the CVD, the template surfaces are uniformly coated with a thin carbon layer, approximately equivalent to a single graphene layer. Subsequent chemical etching removes the templates, yielding a carbon mesosponge (CMS) with spherical mesopores. The CMS



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he has also served as a researcher in the JST PREST “Future Materials” program. His research has focused on the design and synthesis of nanostructured heterogeneous catalysts. Recently, his interests have expanded to include the synthesis, analysis, and application of carbon materials.

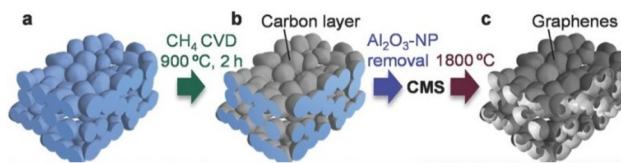


Devis Di Tommaso

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He was promoted to Senior Lecturer in 2020 and to Reader in 2024. His research group develops and applies computational methods based on quantum, classical, and machine learning approaches to study the conversion of small molecules into value-added materials.





**Fig. 1** A schematic of the synthesis of GMS. (a)  $\text{Al}_2\text{O}_3$ -nanoparticles (NP) as a nanosized substrate for CVD. (b) Carbon-coated  $\text{Al}_2\text{O}_3$ -NP. (c) GMS prepared by high-temperature treatment ( $1800\text{ }^\circ\text{C}$ ) of CMS obtained by removing  $\text{Al}_2\text{O}_3$ -NP from carbon-coated  $\text{Al}_2\text{O}_3$ -NP. Reprinted with permission.<sup>13</sup> Copyright Wiley 2016.

is then subjected to heat treatment at  $1800\text{ }^\circ\text{C}$ , promoting the zipping reaction to form a graphene framework with a minimal number of edge sites. Thus, graphene growth on oxide ceramics represents the first critical step in GMS synthesis. However, the detailed reaction mechanisms have been largely unknown. Recent studies have advanced our understanding of graphene growth mechanisms on various types of oxide ceramics, which are discussed in detail in the following sections. Note that thermal stability is a key factor in selecting oxide templates, particularly the ability to maintain surface area and crystal structure under high-temperature conditions above  $600\text{ }^\circ\text{C}$ . This minireview focuses on thermally stable oxides, including as  $\text{Al}_2\text{O}_3$ ,  $\text{MgO}$ ,  $\text{CaO}$ , and  $\text{SiO}_2$ . As an example using a different template, graphene has been synthesized at  $700\text{ }^\circ\text{C}$  using  $\text{CeO}_2$  under photo-assisted conditions.<sup>32</sup>

### 3. Mechanism of graphene growth on ceramic oxide surface

#### 3.1. Aluminium oxide ( $\text{Al}_2\text{O}_3$ ) and magnesium oxide ( $\text{MgO}$ )

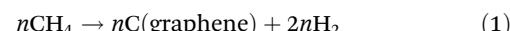
The synthesis of templated carbon utilizing the coking effect on  $\text{Al}_2\text{O}_3$  had been previously reported by Kyotani *et al.*<sup>26</sup>



Hirotomo Nishihara

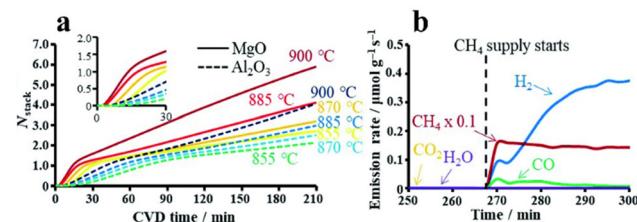
3DC. As the Chief Science Officer, he is dedicated to the industrialization of a novel porous carbon material, graphene mesosponge, which he developed. His research interests include nanoporous materials and carbon-based materials.

Accordingly, in the development of GMS, naturally aggregated  $\gamma\text{-Al}_2\text{O}_3$  nanoparticles were initially employed as a 3D template framework.<sup>13</sup> To form highly crystalline graphene through CVD, thermally stable  $\text{CH}_4$ , which allows for higher reaction temperatures, was used as the carbon source. However, the removal of  $\text{Al}_2\text{O}_3$  template after CVD required either high temperature alkaline melting or hydrofluoric acid (HF) treatment, making the process both costly and environmentally burdensome. In response, the authors explored alternative templates and found that  $\text{MgO}$ , which can be dissolved in hydrochloric acid (HCl), is also suitable for GMS synthesis.<sup>33</sup> Interestingly, the following reaction, where  $\text{CH}_4$  is converted to graphene at high temperatures, occurs on both the solid acid ( $\gamma\text{-Al}_2\text{O}_3$ ) and the solid base ( $\text{MgO}$ ).



Thus, the CVD reaction shown in eqn (1) likely proceeds *via* a mechanism independent of solid acid or base effects.

To investigate this, a detailed analysis of the CVD reaction was performed on the surfaces of both materials.<sup>33</sup> Fig. 2a compares graphene growth rates on both catalyst surfaces at various temperatures. Here, the weight change resulting from graphene deposition on the template during the CVD reaction was measured using the thermogravimetric analyser (TG). The weight gain was then converted to the average number of graphene layers by dividing it by the specific surface area of the template. On either solid surface, the growth rate of the first graphene layer was two to three times faster than that of the second and subsequent layers. The activation energy for forming the first graphene layer was  $114\text{ kJ mol}^{-1}$  for  $\gamma\text{-Al}_2\text{O}_3$  and  $134\text{ kJ mol}^{-1}$  for  $\text{MgO}$ ,<sup>33</sup> both of which are significantly lower than the activation energy for non-catalytic  $\text{CH}_4$  decomposition ( $370\text{--}433\text{ kJ mol}^{-1}$ ).<sup>34</sup> In contrast, the activation energy for forming subsequent layers was higher, at  $234\text{ kJ mol}^{-1}$  for  $\gamma\text{-Al}_2\text{O}_3$  and  $210\text{ kJ mol}^{-1}$  for  $\text{MgO}$  activation energies, respectively.<sup>33</sup> These values are comparable to the activation energy for  $\text{CH}_4$  decomposition on carbon black ( $205\text{--}236\text{ kJ mol}^{-1}$ ),<sup>35</sup> suggesting that subsequent graphene layers form on the first layer. This sequential graphene growth mechanism makes it easy to achieve the uniform coating of single-layer graphene.



**Fig. 2** Analysis of graphene growth reactions *via* CVD using  $\text{CH}_4$  as a precursor on  $\gamma\text{-Al}_2\text{O}_3$  and  $\text{MgO}$ . (a) Plot of the number of graphene layers formed versus CVD reaction time. (b) Gas analysis during the CVD reaction on  $\text{MgO}$ .  $\text{CH}_4$  was introduced to preheated  $\text{MgO}$  at  $900\text{ }^\circ\text{C}$  at the time labelled "CH<sub>4</sub> supply starts". Reprinted with permission.<sup>33</sup> Copyright Royal Society of Chemistry 2021.



Furthermore, as shown in the inset of Fig. 2a, an induction period of 5–10 min was observed from the time the template was exposed to  $\text{CH}_4$  (CVD time = 0) to the onset of carbon deposition. Gas analysis during this induction period (Fig. 2b) detected not only the  $\text{CH}_4$  precursor and the  $\text{H}_2$  product but also the release of  $\text{CO}$ , a common feature observed on both  $\text{Al}_2\text{O}_3$  and  $\text{MgO}$ . These results indicate that  $\text{CH}_4$  extracts oxygen from the surfaces of  $\gamma\text{-Al}_2\text{O}_3$  or  $\text{MgO}$  in the form of  $\text{CO}$ , generating oxygen vacancies that serve as active sites for converting  $\text{CH}_4$  into graphene. Notably, similar CVD reactions were observed on  $\theta\text{-Al}_2\text{O}_3$  as well.<sup>36</sup> These insights into the formation of oxygen vacancy sites and their role in the activation of  $\text{CH}_4$  were further corroborated by density functional theory (DFT) calculations. Fig. 3 summarizes the mechanism of graphene formation on  $\text{Al}_2\text{O}_3$  and  $\text{MgO}$  surfaces.<sup>33</sup>

The initial step of graphene nucleation on the  $\gamma\text{-Al}_2\text{O}_3$  surface was studied in more depth by Di Tommaso and co-workers using computational methods.<sup>37</sup> The process begins with C–H activation, involving proton abstraction by surface oxygen atoms, followed by  $\beta$ -hydrogen elimination, leading to the formation of  $\text{H}_2$ . Fig. 4a shows the energy diagram for dehydrogenation on the most active (100) surface of  $\gamma\text{-Al}_2\text{O}_3$ . While the removal of two hydrogen atoms from  $\text{CH}_4$  to form the  $\text{CH}_2$  adsorbate species ( $\text{CH}_2^*$ ) proceeds with a low energy barrier, the removal of the third hydrogen atom faces a significantly higher energy barrier. This suggests that  $\text{CH}_2^*$  is a key intermediate in the graphene nucleation process. Furthermore, the energy diagram for the coupling reaction of  $\text{CH}_2^*$  on the (100) surface (Fig. 4b) demonstrates that  $\text{CH}_2^*$  readily grows into  $\text{C}_n\text{H}_{2n}^*$  species ( $n = 2\text{--}6$ ). The length of C–C bond length in the  $\text{C}_n\text{H}_{2n}^*$  species on the  $\gamma\text{-Al}_2\text{O}_3$  surface expands with increasing chain length. During the early stages of nucleation, the unsaturated  $\text{CH}_2^*$  groups at both ends of the carbon chain strongly adsorb to the catalyst surface, while

the middle part detaches from the surface, forming a loop-like structure, contributing to the nucleation of graphene.

Di Tommaso and co-workers also adopted a computational approach based on DFT calculations with machine learning forcefield molecular dynamics simulations to investigate the stability and growth investigation of larger graphene clusters,  $\text{C}_n$  ( $n = 16\text{--}26$ ), on  $\text{MgO}$ .<sup>38</sup> Among the various  $\text{C}_n$  clusters examined, the  $\text{C}_{21}$  cluster, which features a bowl-shaped molecular structure with three pentagons and three hexagons alternately arranged around a central hexagon, exhibited unique stability on  $\text{MgO}$  surface. Furthermore, the high electron density at the central hexagon suggests that this cluster acts as a low-mobility nucleation site for graphene growth during CVD. Additionally, it was found that the stability of the  $\text{C}_{21}$  cluster is enhanced when impurities such as Si, Mn, Fe, Ca, or Al are doped onto the  $\text{MgO}$  surface. These computational results suggest that graphene clusters formed in the early stages of CVD tend to adopt specific structures, such as the  $\text{C}_{21}$  cluster.

### 3.2. Calcium oxide ( $\text{CaO}$ )

$\text{CaO}$  is a more cost-effective template compared to  $\text{Al}_2\text{O}_3$  and  $\text{MgO}$ , as it can be readily produced through the low-cost thermal decomposition of enriched calcium carbonate ( $\text{CaCO}_3$ ) and easily removed using hydrochloric acid (HCl). Our group has already demonstrated the synthesis of GMS using  $\text{CaO}$  nanoparticles as templates.<sup>39</sup> Additionally,  $\text{CaO}$  offers higher catalytic activity for  $\text{CH}_4$  decomposition compared to  $\text{Al}_2\text{O}_3$  and  $\text{MgO}$ , allowing CVD to occur at lower temperatures.

A detailed study of the mechanism of graphene formation via CVD using  $\text{CH}_4$  as a precursor on  $\text{CaO}$  template was conducted through experimental and computational methods.<sup>40</sup> DFT calculations revealed that the stepped oxygen sites on the  $\text{CaO}$  (110) surface possess significantly lower energy barriers for  $\text{CH}_4$  dehydrogenation reactions, regardless of the presence of oxygen vacancies (Fig. 5). Specifically, even without oxygen vacancies, the C–H cleavage step of  $\text{CH}_4$  to form  $\text{CH}_3^*$  and  $\text{CH}_2^*$  proceeds spontaneously, and the resulting  $\text{CH}_2^*$  species can subsequently transform into graphene. Indeed, gas emission in the early stage of CVD indicates that, unlike  $\text{Al}_2\text{O}_3$  and  $\text{MgO}$ , there is no induction period on the  $\text{CaO}$  template. That is, graphene formation begins immediately upon  $\text{CH}_4$  contacting the  $\text{CaO}$  surface.<sup>40</sup>

Although the  $\text{CaO}$  surface is active even without oxygen vacancies, analysis of the emission gas composition during CVD reveals that  $\text{CaO}$  releases more  $\text{CO}$  than  $\text{Al}_2\text{O}_3$  and  $\text{MgO}$ . This release continues even after the graphene layer reaches a single layer in thickness. The total  $\text{CO}$  emission during CVD on  $\text{CaO}$  reaches  $4.04 \mu\text{mol m}^{-2}$ .<sup>40</sup> In contrast,  $\text{CO}$  desorption from  $\text{Al}_2\text{O}_3$  and  $\text{MgO}$  terminates before the graphene layer reaches 0.5 layers, with total emissions of only  $0.52$  and  $1.37 \mu\text{mol m}^{-2}$ , respectively. These findings indicate that, on the  $\text{CaO}$  surface, the decomposition of  $\text{CH}_4$  leading to graphene growth and the desorption of surface oxygen as  $\text{CO}$  occur simultaneously. Furthermore,  $\text{CO}$  desorption from the  $\text{CaO}$  surface persists even after the  $\text{CaO}$  surface is completely

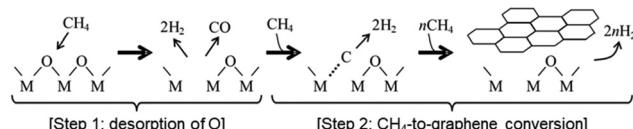


Fig. 3 Mechanism of graphene formation via CVD using  $\text{CH}_4$  as a precursor on  $\gamma\text{-Al}_2\text{O}_3$  and  $\text{MgO}$  ( $\text{M} = \text{Al}$  or  $\text{Mg}$ ).

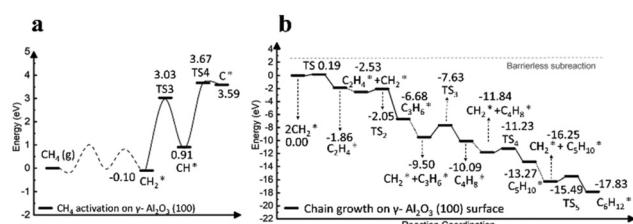
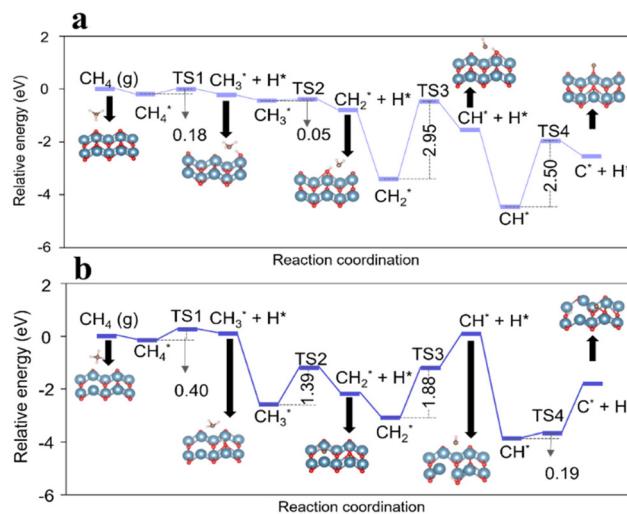


Fig. 4 Energy profiles of (a) the complete  $\text{CH}_4^*$  dehydrogenation and (b) the formation of  $\text{C}_n\text{H}_{2n}^*$  ( $n = 2\text{--}6$ ) species via  $\text{CH}_2^*$  coupling on the  $\gamma\text{-Al}_2\text{O}_3$  (100) surface. Adapted from ref. 37 with modifications.





**Fig. 5** The energy profiles for the C–H activation on the (a) pristine CaO (111) surface and (b) CaO (111) surface with oxygen vacancy sites. The blue, red, brown, and white balls represent Ca, O, C, and H atoms, respectively. Adapted from ref. 40 with modifications.

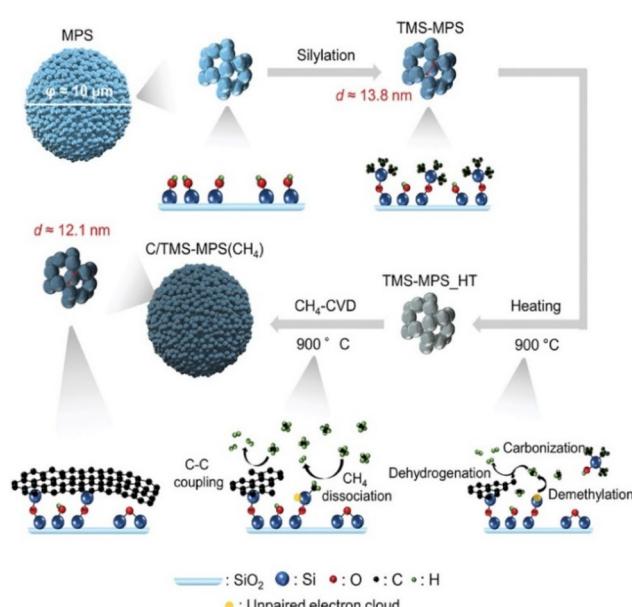
coated with graphene. To elucidate this mechanism, the interaction between the formed graphene layer and the underlying CaO was calculated. It was found that the presence of the surface graphene layer destabilizes the oxygen atoms in CaO and induces the further transfer of oxygen to the outer surface of the graphene layer. Following this oxygen transfer process,  $\text{CH}_4$  molecules preferentially bind to the acquired oxygen, generating  $\text{CH}_3\text{OH}$  *via* the reaction, which is further decomposed at CVD temperatures to produce CO. Additionally, the calculation results indicate that the energy required for oxygen transfer on the stepped CaO (110) surface is significantly lower than that on the MgO (110) surface, highlighting a unique oxygen desorption pathway specific to CaO. Following oxygen desorption from the graphene coated CaO surface, the CaO structure undergoes rearranges itself, restricting further oxygen desorption from neighbouring sites. Consequently, CO emissions cease experimentally after a certain period.

### 3.3. Silicon Dioxide ( $\text{SiO}_2$ )

Although  $\text{Al}_2\text{O}_3$ ,  $\text{MgO}$ , and  $\text{CaO}$  exhibit excellent catalytic performance for graphene formation, these templates face challenges in forming complex nanostructures. In contrast,  $\text{SiO}_2$  is considered one of the most ideal ceramic oxide candidates for nanostructure formation, as it can form a diverse range of nanostructures, including monodisperse nanoparticles, core-shell particles, nanofibers, silica aerogels, and mesoporous silica. However, the  $\text{SiO}_2$  surface has negligible catalytic activity for graphene formation *via*  $\text{CH}_4$  decomposition. Hoshikawa *et al.* found that a modification of  $\text{SiO}_2$  surfaces with trimethylsilyl groups (TMS) significantly enhanced their catalysis for CVD using acetylene ( $\text{C}_2\text{H}_2$ ) as a carbon source.<sup>41</sup> Based on this finding, trimethylsilyl functionalized micro-spherical porous silica (TMS–MPS) was employed as a core material to convert  $\text{CH}_4$  into graphene, thereby synthesizing GMS.<sup>42</sup>

Furthermore, we analysed the reaction mechanism of  $\text{CH}_4$  conversion to graphene on the surface of TMS–MPS.<sup>43</sup>

Fig. 6 illustrates the scheme of TMS modification on MPS and graphene coating *via* CVD using  $\text{CH}_4$  as a carbon source. After replacing the silanol groups ( $\text{Si}-\text{OH}$ ) on the silica surface with TMS groups, the TMS groups are converted to Si radicals and polycyclic aromatic hydrocarbons (PAHs) at 900 °C. The presence of Si radicals substantially enhances carbon deposition and lowers the initial graphene formation temperature from 885 °C on pristine  $\text{SiO}_2$  to 720 °C. Carbon deposition on TMS–MPS is five times higher than on MPS at 900 °C, demonstrating the catalytic effect induced by Si radicals. DFT calculations also reveal that Si radicals act as active sites for  $\text{CH}_4$  dissociation. Additionally, both experimental and computational results demonstrated Si radicals promote the growth of the second layers even when the  $\text{SiO}_2$  surface is already coated with a single graphene layer. Furthermore, unlike  $\text{Al}_2\text{O}_3$ ,  $\text{MgO}$  and  $\text{CaO}$ , no CO release was detected on either MPS or TMS–MPS, indicating that oxygen vacancies are not formed in these systems. Thus, it is proposed that the mechanism of  $\text{CH}_4$  activation on TMS– $\text{SiO}_2$  is fundamentally different from that of other oxide ceramics discussed above.

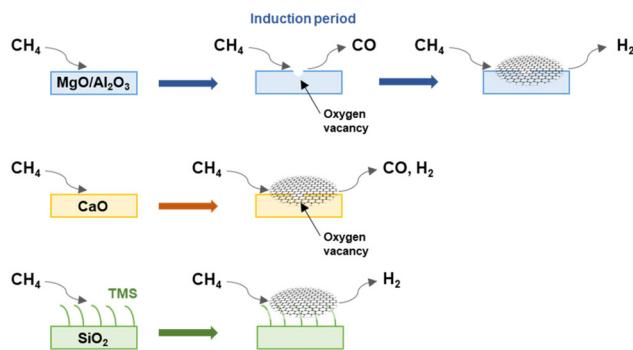


**Fig. 6** Trimethylsilylation of the MPS template (top) and modification of the graphene coating process *via* CVD using  $\text{CH}_4$  as a precursor (bottom). The  $\varphi$  and  $d$  denote the diameter and pore size of samples, respectively.<sup>43</sup>

**Table 1** Comparison of CVD mechanism using  $\text{CH}_4$  as a carbon source on different kinds of oxide ceramics

	Induction period	Active sites	CO generation
$\text{Al}_2\text{O}_3$ , $\text{MgO}$	Yes	Oxygen vacancies	Yes
CaO	No	Surface oxygen sites	Yes
TMS modified $\text{SiO}_2$	No	Si radicals	No





**Fig. 7** Graphene formation via CVD using  $\text{CH}_4$  as a carbon source on  $\text{Al}_2\text{O}_3$ ,  $\text{MgO}$ ,  $\text{CaO}$ , and  $\text{SiO}_2$ .

## 4. Conclusions

This minireview has summarized recent progress on the mechanisms of graphene growth on oxide ceramic substrates *via* the chemical vapor deposition process (Table 1 and Fig. 7).  $\text{Al}_2\text{O}_3$  and  $\text{MgO}$  facilitate graphene formation through the oxygen vacancy-mediated  $\text{CH}_4$  decomposition. During the induction period preceding graphene growth,  $\text{CH}_4$  extracts oxygen from the substrate, releasing  $\text{CO}$  and generating oxygen vacancies as active sites *in situ*. In contrast,  $\text{CaO}$  supports spontaneous graphene growth without an induction period, accompanied by the release of a significant amount of  $\text{CO}$  through the unique oxygen transfer mechanism. Meanwhile, pristine  $\text{SiO}_2$  lacks activity for methane conversion; however, surface modification with trimethylsilyl groups generates Si radicals *in situ* during heat treatment, which promote  $\text{CH}_4$  activation and enable graphene growth. In conclusion, these findings emphasize that activation mechanisms vary significantly depending on the substrate material, even when using the same  $\text{CH}_4$  as a carbon source, highlighting the importance of selecting an appropriate system based on the intended application.

From the perspective of templates for graphene synthesis, oxide ceramics are characterized by their nanostructure-forming capabilities and high thermal stability, making them particularly valuable for fabricating three-dimensional graphene, which holds the potential to play a crucial role in fields such as electronics, energy, and biotechnology. Investigating the distinct CVD mechanisms across various templates expands the library of viable candidates and enables precise control over domain size and defect density of 3D graphene, which are key parameters for tuning material performance. It also opens new possibilities for synthesis on unconventional substrates and under non-standard conditions, thereby broadening the potential applications of graphene-based materials.

In addition, it is worth noting that the CVD process using  $\text{CH}_4$  offers inherent sustainability advantages. The core reaction ( $\text{CH}_4 \rightarrow \text{C} + 2\text{H}_2$ ) not only provides carbon for graphene formation but also generates hydrogen that can be classified as turquoise hydrogen. This enables efficient utilization of  $\text{CH}_4$  in terms of resource efficiency and carbon footprint,

further reinforcing the appeal of CVD approach as a green synthetic platform.

Looking ahead, the discovery of new template materials, as well as innovations in carbon sources and deposition techniques, is expected to drive further advancements in 3D graphene synthesis. Consequently, elucidating the fundamental mechanisms of graphene growth, including carbon nucleation and crystallization processes, will continue to be a critical research focus. We hope that this minireview will serve as a foundation for further advancements in this field.

## Author contributions

Writing – original draft: H. Z.; Writing – review & editing: M. Z., T. Y., D. D. T., H. N.

## Data availability

No primary research results, software or code have been included and no new data were generated or analysed as part of this review.

## Conflicts of interest

There are no conflicts to declare.

## Acknowledgements

This work was supported by JSPS KAKENHI Grant No. 23H00227; JST A-STEP Grant No. JPMJTR22T6; JST CREST Grant No. JPMJCR24S6; Council for Science, Technology and Innovation (CSTI), Cross-ministerial Strategic Innovation Promotion Program (SIP), the 3rd period of SIP “Creating a materials innovation ecosystem for industrialization” Grant No. JPJ012307 (Funding agency: NIMS); Kondo Memorial Foundation Grant No. 2023-01; “Crossover Alliance to Create the Future with People, Intelligence and Materials” from MEXT, Japan; the Cooperative Research Program of “NJR Mater. & Dev.”; UK’s Royal Society International Exchanges Cost Share (IEC|R3|193106).

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